

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application:

LISTING OF CLAIMS:

Claims 1-26 (canceled).

27. (currently amended): A semiconductor device comprising:
a semiconductor substrate, and
a metal wiring and an interlayer dielectric film which are formed on said semiconductor substrate,
said interlayer dielectric film including a multi-layered structure consisting of:
a diffusion barrier film preventing diffusion of the metal out of said metal wiring,
an adhesive film formed directly on said diffusion barrier film, and
a low dielectric constant film formed directly on said adhesive film,
said adhesive film being constituted by a silicon-based compound having an aromatic ring in a molecule of said silicon-based compound, and
said low dielectric constant film being constituted essentially by an organic low dielectric constant material having a specific dielectric constant not greater than 4, and
said organic low dielectric constant material being a silicon-containing organic compound.

28. (previously presented): The semiconductor device as set forth in Claim 27, wherein said diffusion barrier film is constituted by SiCN.

29. (previously presented): The semiconductor device as set forth in Claim 27, wherein said silicon-based compound includes a benzocyclobutene unit in a molecule thereof.

30. (previously presented): The semiconductor device as set forth in Claim 27, wherein said silicon-based compound contains a silylene unit in a molecule thereof.

31. (previously presented): The semiconductor device as set forth in Claim 27, wherein said silicon-based compound is a polymer formed through polymerization of a monomer containing a divinylsiloxane bisbenzocyclobutene unit.

32. (currently amended): The semiconductor device as set forth in Claim 27, wherein said ~~organic low dielectric constant material~~ silicon-containing organic compound is methylsilsesquioxane.

33. (canceled).

34. (currently amended): The semiconductor device as set forth in Claim 27, wherein said ~~organic low dielectric constant material~~ silicon-containing organic compound is a SiOC.

35. (previously presented): The semiconductor device as set forth in Claim 27, wherein said interlayer dielectric film is formed on said metal wiring.